WINSOURCE ELECTRONICS

THE DATASHEET OF

AD660BRZ

Monolithic 16-Bit Serial/Byte DACPORT

AD660

FEATURES

Complete 16-bit digital-to-analog function
- **On-chip output amplifier**
- **On-chip buried Zener voltage reference**
- **±1 LSB integral linearity**

15-bit monotonic over temperature
Microprocessor compatible
- **Serial or byte input**
- **Double-buffered latches**
- **Fast (40 ns) write pulse**

Asynchronous clear (to 0 V) function
Serial output pin facilitates daisy-chaining
Unipolar or bipolar output
Low glitch: 15 nV-s
Low THD + N: 0.009%

FUNCTIONAL BLOCK DIAGRAM

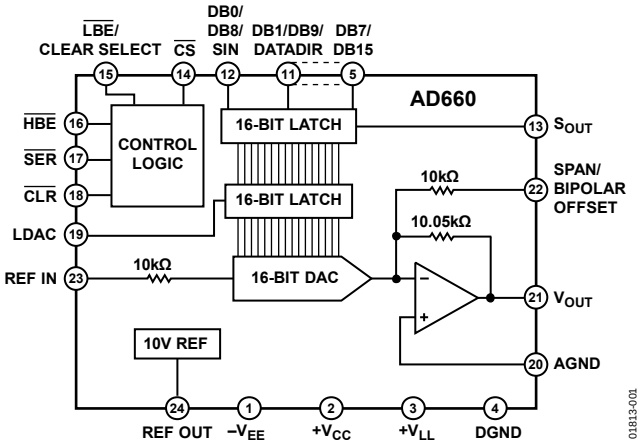

Figure 1.

GENERAL DESCRIPTION

The AD660 DACPORT® is a complete 16-bit monolithic digital-to-analog converter with an on-board voltage reference, double-buffered latches, and an output amplifier. It is manufactured on the Analog Devices, Inc., BiMOS II process. This process allows the fabrication of low power CMOS logic functions on the same chip as high precision bipolar linear circuitry.

The AD660 architecture ensures 15-bit monotonicity over time and temperature. Integral and differential nonlinearity is maintained at ±0.003% maximum. The on-chip output amplifier provides a voltage output settling time of 10 µs to within ½ LSB for a full-scale step.

The AD660 has an extremely flexible digital interface. Data can be loaded into the AD660 in serial mode or as two 8-bit bytes. This is made possible by two digital input pins that have dual functions. The serial mode input format is pin selectable to be MSB or LSB first. The serial output pin allows the user to daisy-chain several AD660 devices by shifting the data through the input latch into the next DAC, thus minimizing the number of control lines required to SIN, $\overline{CS}$ and LDAC. The byte mode input format is also flexible in that the high byte or low byte data can be loaded first. The double buffered latch structure eliminates data skew errors and provides for simultaneous updating of DACs in a multiDAC system.

The AD660 is available in five grades. AN and BN versions are specified from −40°C to +85°C and are packaged in a 24-lead 300 mil plastic DIP. AR and BR versions are also specified from −40°C to +85°C and are packaged in a 24-lead SOIC. The SQ version is packaged in a 24-lead 300 mil CERDIP package and is also available compliant to MIL-STD-883. Refer to the AD660SQ/883B military data sheet for specifications and test conditions.

PRODUCT HIGHLIGHTS

1. The AD660 is a complete 16-bit DAC, with a voltage reference, double-buffered latches, and an output amplifier on a single chip.
2. The internal buried Zener reference is laser trimmed to 10.000 V with a ±0.1% maximum error and a temperature drift performance of ±15 ppm/°C. The reference is available for external applications.
3. The output range of the AD660 is pin programmable and can be set to provide a unipolar output range of 0 V to 10 V or a bipolar output range of −10 V to +10 V. No external components are required.
4. The AD660 is both dc and ac specified. DC specifications include ±1 LSB INL and ±1 LSB DNL errors. AC specifications include 0.009% THD + N and 83 dB SNR.
5. The double-buffered latches on the AD660 eliminate data skew errors and allow simultaneous updating of DACs in multiDAC applications.
6. The clear function can asynchronously set the output to 0 V regardless of whether the DAC is in unipolar or bipolar mode.
7. The output amplifier settles within 10 µs to ±½ LSB for a full-scale step and within 2.5 µs for a 1 LSB step over temperature. The output glitch is typically 15 nV-s when a full-scale step is loaded.

Rev. B
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REVISION HISTORY

6/08—Rev. A to Rev. B

Updated Format ... Universal
Updated Pin Name MSB/$\overline{\text{LSB}}$ to DATADIR Throughout ... 1
Updated Pin Name $\overline{\text{UNI}}$/BIP CLEAR to CLEAR SELECT Throughout ... 1
Changes to Table 1 ... 3
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SPECIFICATIONS

T_A = 25°C, $+V_{CC}$ = 15 V, $-V_{EE}$ = −15 V, $+V_{LL}$ = 5 V unless otherwise noted.

Table 1.

	AD660AN/AR/SQ			AD660BN/BR			
Parameter	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Unit**
RESOLUTION	16			16			Bits
DIGITAL INPUTS (T_{MIN} to T_{MAX})							
V_{IH} (Logic 1)	2.0		5.5	2.0		5.5	V
V_{IL} (Logic 0)	0		0.8	0		0.8	V
I_{IH} (V_{IH} = 5.5 V)	−10		+10	−10		+10	µA
I_{IL} (V_{IL} = 0 V)	−10		+10	−10		+10	µA
TRANSFER FUNCTION CHARACTERISTICS[1]							
Integral Nonlinearity							
Bipolar Operation	−2		+2	−1		+1	LSB
T_{MIN} to T_{MAX}	−4		+4	−2		+2	LSB
Unipolar Operation	−2		+2	−1		+1.5	LSB
T_{MIN} to T_{MAX}	−4		+4	−2		+2	LSB
Differential Nonlinearity	−2		+2	−1		+1	LSB
T_{MIN} to T_{MAX}	−4		+4	−2		+2	LSB
Monotonicity Over Temperature	14			15			Bits
Gain Error[2, 3]	−0.1		+0.1	−0.1		+0.1	% of FSR
Gain Drift (T_{MIN} to T_{MAX})			25			15	ppm/°C
DAC Gain Error[4]	−0.05		+0.05	−0.05		+0.05	% of FSR
DAC Gain Drift[4]			10			10	ppm/°C
Unipolar Offset	−2.5		+2.5	−2.5		+2.5	mV
Unipolar Offset Drift (T_{MIN} to T_{MAX})			3			3	ppm/°C
Bipolar Zero Error	−7.5		+7.5	−7.5		+7.5	mV
Bipolar Zero Error Drift (T_{MIN} to T_{MAX})			5			5	ppm/°C
REFERENCE INPUT							
Input Resistance	7	10	13	7	10	13	kΩ
Bipolar Offset Input Resistance	7	10	13	7	10	13	kΩ
REFERENCE OUTPUT							
Voltage	9.99	10.00	10.01	9.99	10.00	10.01	V
Drift			25			15	ppm/°C
External Current[5]	2	4		2	4		mA
Capacitive Load			1000			1000	pF
Short-Circuit Current		25			25		mA
OUTPUT CHARACTERISTICS							
Output Voltage Range							
Unipolar Configuration	0		+10	0		+10	V
Bipolar Configuration	−10		+10	−10		+10	V
Output Current	5			5			mA
Capacitive Load			1000			1000	pF
Short-Circuit Current		25			25		mA

Parameter	AD660AN/AR/SQ Min	AD660AN/AR/SQ Typ	AD660AN/AR/SQ Max	AD660BN/BR Min	AD660BN/BR Typ	AD660BN/BR Max	Unit
POWER SUPPLIES							
Voltage							
$+V_{CC}$[6]	+13.5		+16.5	+13.5		+16.5	V
$-V_{EE}$[6]	−13.5		−16.5	−13.5		−16.5	V
$+V_{LL}$	+4.5		+5.5	+4.5		+5.5	V
Current (No Load)							
I_{CC}		+12	+18		+12	+18	mA
I_{EE}		−12	−18		−12	−18	mA
I_{LL}							
@ V_{IH} = 5 V, V_{IL} = 0 V		0.3	2		0.3	2	mA
@ V_{IH} = 2.4 V, V_{IL} = 0.4 V		3	7.5		3	7.5	mA
Power Supply Sensitivity		1	2		1	2	ppm/%
Power Dissipation (Static, No Load)		365	625		365	625	mW
TEMPERATURE RANGE							
Specified Performance (A, B)	−40		+85	−40		+85	°C
Specified Performance (S)	−55		+125				°C

[1] For 16-bit resolution, 1 LSB = 0.0015% of FSR. For 15-bit resolution, 1 LSB = 0.003% of FSR. For 14-bit resolution, 1 LSB = 0.006% of FSR. FSR stands for full-scale range and is 10 V in a unipolar mode and 20 V in bipolar mode.
[2] Gain error and gain drift are measured using the internal reference. The internal reference is the main contributor to gain drift. If lower gain drift is required, the AD660 can be used with a precision external reference such as the AD587, AD586, or AD688.
[3] Gain error is measured with fixed 50 Ω resistors as shown in the Theory of Operation section. Eliminating these resistors increases the gain error by 0.25% of FSR (unipolar mode) or 0.50% of FSR (bipolar mode).
[4] DAC gain error and drift are measured with an external voltage reference. They represent the error contributed by the DAC alone, for use with an external reference.
[5] External current is defined as the current available in addition to that supplied to REF IN and SPAN/BIPOLAR OFFSET on the AD660.
[6] Operation on ±12 V supplies is possible using an external reference such as the AD586 and reducing the output range. Refer to the Internal/External Reference Use section.

AC PERFORMANCE CHARACTERISTICS

With the exception of total harmonic distortion + noise (THD + N) and signal-to-noise (SNR) ratio, these characteristics are included for design guidance only and are not subject to test. THD + N and SNR are 100% tested.

$T_{MIN} \le T_A \le T_{MAX}$, $+V_{CC}$ = 15 V, $-V_{EE}$ = −15 V, $+V_{LL}$ = 5 V except where noted.

Table 2.

Parameter	Limit	Unit	Test Conditions/Comments
OUTPUT SETTLING TIME	13	µs max	20 V step, T_A = 25°C
(Time to ±0.0008% FS	8	µs typ	20 V step, T_A = 25°C
with 2 kΩ, 1000 pF Load)	10	µs typ	20 V step, $T_{MIN} \le T_A \le T_{MAX}$
	6	µs typ	10 V step, T_A = 25°C
	8	µs typ	10 V step, $T_{MIN} \le T_A \le T_{MAX}$
	2.5	µs typ	1 LSB step, $T_{MIN} \le T_A \le T_{MAX}$
TOTAL HARMONIC DISTORTION + NOISE			
A, B, S Grade	0.009	% max	0 dB, 990.5 Hz, sample rate = 96 kHz, T_A = 25°C
A, B, S Grade	0.056	% max	−20 dB, 990.5 Hz, sample rate = 96 kHz, T_A = 25°C
A, B, S Grade	5.6	% max	−60 dB, 990.5 Hz, sample rate = 96 kHz, T_A = 25°C
SIGNAL-TO-NOISE RATIO	83	dB min	T_A = 25°C
DIGITAL-TO-ANALOG GLITCH IMPULSE	15	nV-s typ	DAC alternately loaded with 0x8000 and 0x7FFF
DIGITAL FEEDTHROUGH	2	nV-s typ	DAC alternately loaded with 0x0000 and 0xFFFF, $\overline{CS}$ high
OUTPUT NOISE VOLTAGE			
Density (1 kHz to 1 MHz)	120	nV/√Hz typ	Measured at V_{OUT}, 20 V span, excludes reference
REFERENCE NOISE	125	nV/√Hz typ	Measured at REF OUT

TIMING CHARACTERISTICS

$+V_{CC}$ = 15 V, $-V_{EE}$ = −15 V, $+V_{LL}$ = 5 V, V_{HIGH} = 2.4 V, V_{LOW} = 0.4 V.

Table 3.

Parameter	Limit at T_A = 25°C	Limit at T_A = −55°C to +125°C	Unit
BYTE LOAD (see Figure 2)			
$t_{\overline{CS}}$	40	50	ns min
t_{DS}	40	50	ns min
t_{DH}	0	10	ns min
$t_{\overline{BES}}$	40	50	ns min
$t_{\overline{BEH}}$	0	10	ns min
t_{LH}	80	100	ns min
t_{LW}	40	50	ns min
SERIAL LOAD (see Figure 3)			
t_{CLK}	80	100	ns min
t_{LOW}	30	50	ns min
t_{HIGH}	30	50	ns min
t_{SS}	0	10	ns min
t_{DS}	40	50	ns min
t_{DH}	0	10	ns min
t_{SH}	0	10	ns min
t_{LH}	80	100	ns min
t_{LW}	40	50	ns min
ASYNCHRONOUS CLEAR TO BIPOLAR OR UNIPOLAR ZERO (see Figure 4)			
$t_{\overline{CLR}}$	80	110	ns min
t_{SET}	80	110	ns min
t_{HOLD}	0	10	ns min
SERIAL OUT (see Figure 5)			
t_{PROP}	50	100	ns min
t_{DS}	50	80	ns min

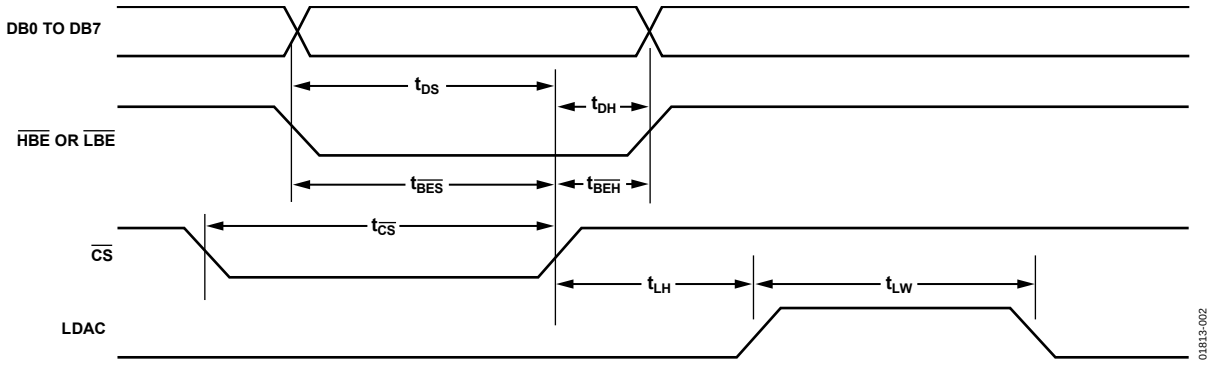


Figure 2. AD660 Byte Load Timing

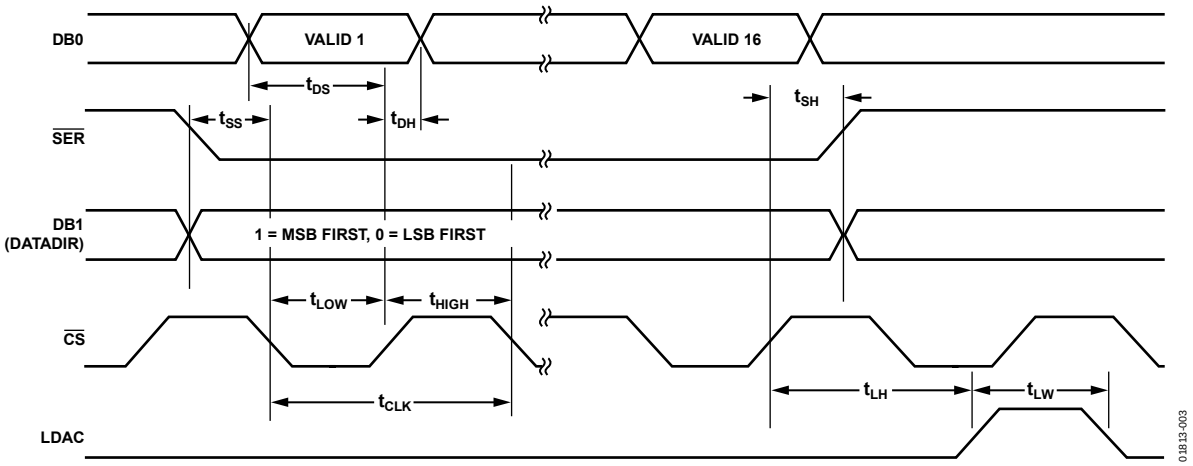


Figure 3. AD660 Serial Load Timing

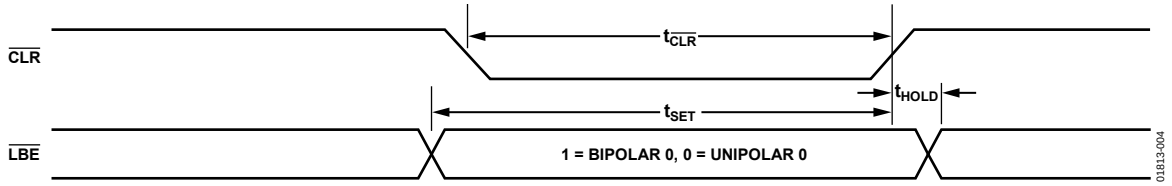


Figure 4. Asynchronous Clear to Bipolar or Unipolar Zero

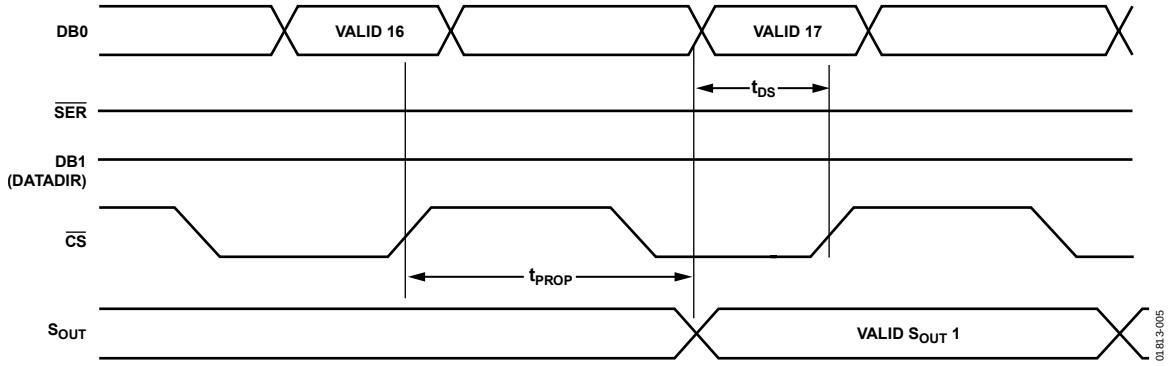


Figure 5. Serial Out Timing

ABSOLUTE MAXIMUM RATINGS

Table 4.

Parameter	Rating
$+V_{CC}$ to AGND	−0.3 V to +17.0 V
$-V_{EE}$ to AGND	+0.3 V to −17.0 V
$+V_{LL}$ to DGND	−0.3 V to +7 V
AGND to DGND	±1 V
Digital Inputs (Pin 5 through Pin 23) to DGND	−1.0 V to +7.0 V
REF IN to AGND	±10.5 V
SPAN/BIPOLAR OFFSET to AGND	±10.5 V
REF OUT, V_{OUT}	Indefinite short to AGND, DGND, $+V_{CC}$, $-V_{EE}$, and $+V_{LL}$
Power Dissipation (Any Package)	
To +60°C	1000 mW
Derates Above +60°C	8.7 mW/°C
Storage Temperature	−65°C to +150°C
Lead Temperature	JEDEC industry standard
Soldering	J-STD-020

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

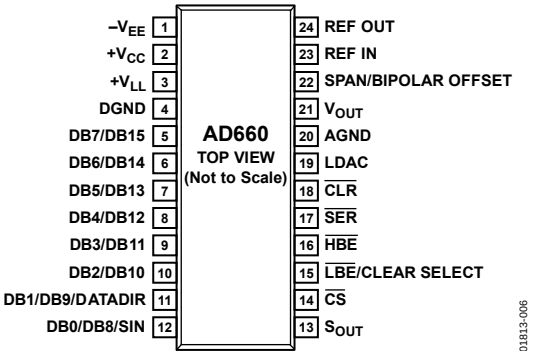


Figure 6. Pin Configuration

Table 5. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	$-V_{EE}$	Negative Analog Supply Pin
2	$+V_{CC}$	Positive Analog Supply Pin
3	$+V_{LL}$	Digital Supply Pin
4	DGND	Digital Ground Reference Pin
5	DB7/DB15	DB7 and DB15 Byte Load Data Input Pin
6	DB6/DB14	DB6 and DB14 Byte Load Data Input Pin
7	DB5/DB13	DB5 and DB13 Byte Load Data Input Pin
8	DB4/DB12	DB4 and DB12 Byte Load Data Input Pin
9	DB3/DB11	DB3 and DB11 Byte Load Data Input Pin
10	DB2/DB10	DB2 and DB10 Byte Load Data Input Pin
11	DB1/DB9/DATADIR	DB1 and DB9 Byte Load Data Input Pin/MSB or $\overline{\text{LSB}}$ First Data Direction Serial Input Select Pin
12	DB0/DB8/SIN	DB0 and DB8 Byte Load Data Input Pin/Serial Data Input Pin
13	S_{OUT}	Serial Data Output Pin
14	$\overline{\text{CS}}$	Chip Select Pin
15	$\overline{\text{LBE}}$/CLEAR SELECT	Low Byte Enable Pin/$\overline{\text{Unipolar}}$ or Bipolar Clear Select Pin
16	$\overline{\text{HBE}}$	High Byte Enable Pin
17	$\overline{\text{SER}}$	Serial Input Enable Pin
18	$\overline{\text{CLR}}$	Output Clear Pin
19	LDAC	Load DAC Pin
20	AGND	Analog Ground Reference Pin
21	V_{OUT}	Voltage Output Pin
22	SPAN/BIPOLAR OFFSET	Output Span Configuration Pin
23	REF IN	External Reference Voltage Input Pin
24	REF OUT	Internal Reference Voltage Output Pin

TERMINOLOGY

Integral Nonlinearity
Integral nonlinearity is the maximum deviation of the actual, adjusted DAC output from the ideal analog output (a straight line drawn from 0 to FS − 1 LSB) for any bit combination. This is also referred to as relative accuracy.

Differential Nonlinearity
Differential nonlinearity is the measure of the change in the analog output, normalized to full scale, associated with a 1 LSB change in the digital input code. Monotonic behavior requires that the differential linearity error be greater than or equal to −1 LSB over the temperature range of interest.

Monotonicity
A DAC is monotonic if the output either increases or remains constant for increasing digital inputs with the result that the output is always a single-valued function of the input.

Gain Error
Gain error is a measure of the output error between an ideal DAC and the actual device output with all 1s loaded after offset error has been adjusted out.

Offset Error
Offset error is a combination of the offset errors of the voltage-mode DAC and the output amplifier and is measured with all 0s loaded in the DAC.

Bipolar Zero Error
When the AD660 is connected for bipolar output and 10…000 is loaded in the DAC, the deviation of the analog output from the ideal midscale value of 0 V is called the bipolar zero error.

Drift
Drift is the change in a parameter (such as gain, offset, and bipolar zero) over a specified temperature range. The drift temperature coefficient, specified in ppm/°C, is calculated by measuring the parameter at T_{MIN}, 25°C, and T_{MAX}, and dividing the change in the parameter by the corresponding temperature change.

Total Harmonic Distortion + Noise
Total harmonic distortion + noise (THD + N) is defined as the ratio of the square root of the sum of the squares of the values of the harmonics and noise to the value of the fundamental input frequency. It is usually expressed in percent (%).

THD + N is a measure of the magnitude and distribution of linearity error, differential linearity error, quantization error, and noise. The distribution of these errors may be different, depending upon the amplitude of the output signal. Therefore, to be the most useful, THD + N should be specified for both large and small signal amplitudes.

Signal-To-Noise Ratio
The signal-to-noise ratio is the ratio of the amplitude of the output when a full-scale signal is present to the output with no signal present. The signal-to-noise ratio is measured in decibels (dB).

Digital-To-Analog Glitch Impulse
Digital-to-analog glitch impulse is the amount of charge injected from the digital inputs to the analog output when the inputs change state. This is measured at half scale when the DAC switches around the MSB and as many as possible switches change state, that is, from 011…111 to 100…000.

Digital Feedthrough
When the DAC is not selected (that is, $\overline{CS}$ is held high), high frequency logic activity on the digital inputs is capacitively coupled through the device to show up as noise on the V_{OUT} pin. This noise is digital feedthrough.

THEORY OF OPERATION

The AD660 uses an array of bipolar current sources with MOS current steering switches to develop a current proportional to the applied digital word, ranging from 0 mA to 2 mA. A segmented architecture is used, where the most significant four data bits are thermometer decoded to drive 15 equal current sources. The lesser bits are scaled using a R-2R ladder, then applied together with the segmented sources to the summing node of the output amplifier. The internal span/bipolar offset resistor can be connected to the DAC output to provide a 0 V to 10 V span, or it can be connected to the reference input to provide a −10 V to +10 V span.

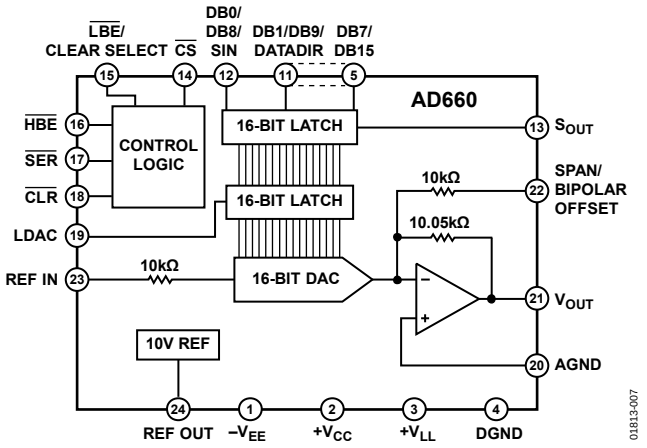


Figure 7. Functional Block Diagram

ANALOG CIRCUIT CONNECTIONS

Internal scaling resistors provided in the AD660 can be connected to produce a unipolar output range of 0 V to 10 V or a bipolar output range of −10 V to +10 V. Gain and offset drift are minimized in the AD660 because of the thermal tracking of the scaling resistors with other device components.

UNIPOLAR CONFIGURATION

The configuration shown in Figure 8 provides a unipolar 0 V to 10 V output range. In this mode, 50 Ω resistors are tied between the SPAN/BIPOLAR OFFSET terminal (Pin 22) and V_{OUT} (Pin 21), and between REF OUT (Pin 24) and REF IN (Pin 23). It is possible to use the AD660 without any external components by tying Pin 24 directly to Pin 23 and Pin 22 directly to Pin 21. Eliminating these resistors increases the gain error by 0.25% of FSR.

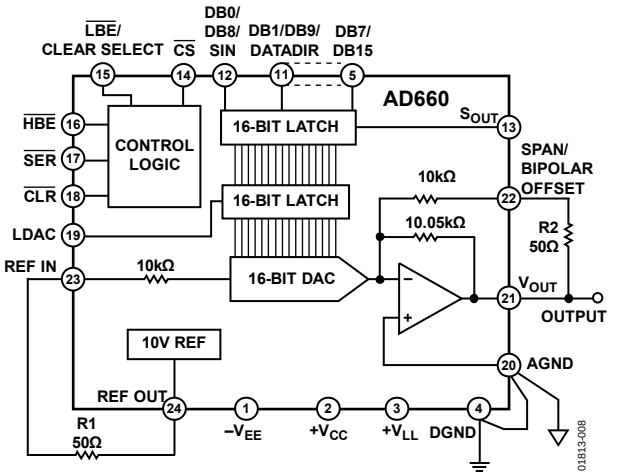


Figure 8. 0 V to 10 V Unipolar Voltage Output

If it is desired to adjust the gain and offset errors to zero, this can be accomplished using the circuit shown in Figure 9. The adjustment procedure is as follows:

1. Zero adjust.
   Turn all bits off and adjust the zero trimmer, R4, until the output reads 0.000000 V (1 LSB = 153 μV).
2. Gain adjust.
   Turn all bits on and adjust the gain trimmer, R1, until the output is 9.999847 V. (Full scale is adjusted to 1 LSB less than the nominal full scale of 10.000000 V.)

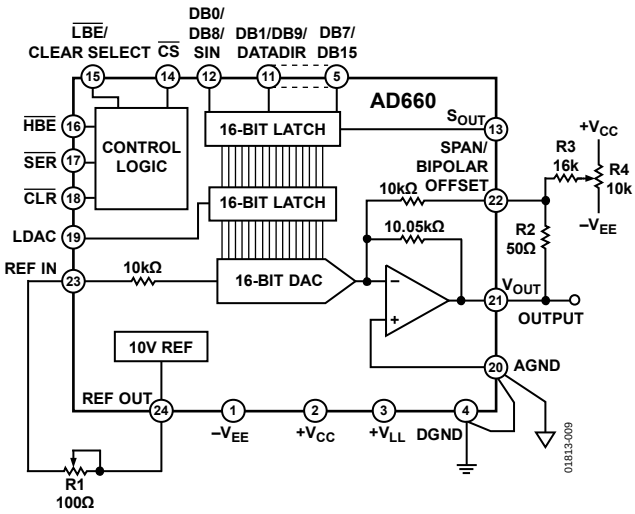


Figure 9. 0 V to 10 V Unipolar Voltage Output with Gain and Offset Adjustment

BIPOLAR CONFIGURATION

The circuit shown in Figure 10 provides a bipolar output voltage from −10.000000 V to +9.999694 V with positive full scale occurring with all bits on. As in the unipolar mode, Resistor R1 and Resistor R2 can be eliminated altogether to provide AD660 bipolar operation without any external components. Eliminating these resistors increases the gain error by 0.50% of FSR in bipolar mode.

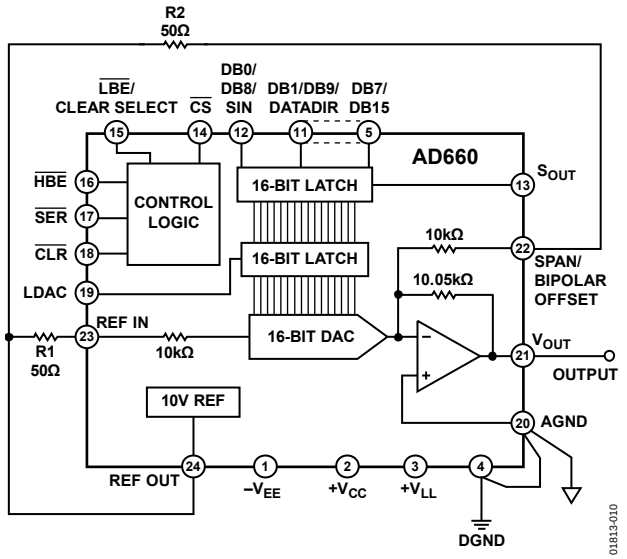


Figure 10. ±10 V Bipolar Voltage Output

Gain offset and bipolar zero errors can be adjusted to zero using the circuit shown in Figure 11 as follows:

1. Offset adjust.
   Turn off all bits. Adjust the trimmer, R2, to give 10.000000 V output.
2. Gain adjust.
   Turn all bits on and adjust R1 to give a reading of 9.999694 V.
3. Bipolar zero adjust (optional).
   In applications where an accurate zero output is required, set the MSB on, all other bits off, and readjust R2 for 0 V output.

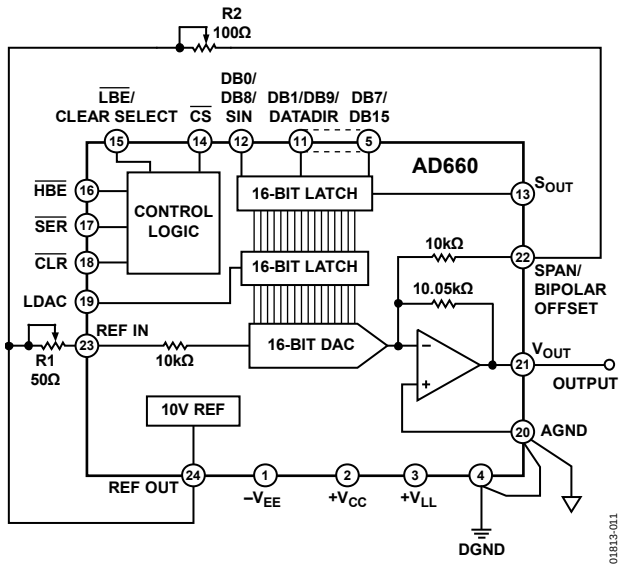


Figure 11. ±10 V Bipolar Voltage Output with Gain and Offset Adjustment

Note that using external resistors introduces a small temperature drift component beyond that inherent in the AD660. The internal resistors are trimmed to ratio-match and temperature-track other resistors on-chip, even though their absolute tolerances are ±20% and absolute temperature coefficients are approximately −50 ppm/°C. In the case that external resistors are used, the temperature coefficient mismatch between internal and external resistors, multiplied by the sensitivity of the circuit to variations in the external resistor value, is the resultant additional temperature drift.

INTERNAL/EXTERNAL REFERENCE USE

The AD660 has an internal low noise buried Zener diode reference that is trimmed for absolute accuracy and temperature coefficient. This reference is buffered and optimized for use in a high speed DAC and gives long-term stability equal or superior to the best discrete Zener diode references. The performance of the AD660 is specified with the internal reference driving the DAC and with the DAC alone (for use with a precision external reference).

The internal reference has sufficient buffering to drive external circuitry in addition to the reference currents required for the DAC (typically 1 mA to REF IN and 1 mA to SPAN/BIPOLAR OFFSET). A minimum of 2 mA is available for driving external loads. The AD660 reference output should be buffered with an external op amp if it is required to supply more than 4 mA total current. The reference is tested and guaranteed to ±0.2% maximum error.

It is also possible to use external references other than 10 V with slightly degraded linearity specifications. The recommended range of reference voltages is 5 V to 10.24 V, which allows 5 V, 8.192 V, and 10.24 V ranges to be used. For example, by using the AD586 5 V reference, outputs of 0 V to 5 V unipolar or ±5 V bipolar can be realized. Using the AD586 voltage reference makes it possible to operate the AD660 with ±12 V supplies with 10% tolerances.

Figure 12 shows the AD660 using the AD586 precision 5 V reference in the bipolar configuration. The highest grade AD586MN is specified with a drift of 2 ppm/°C, which is a 7.5× improvement over the AD660 internal reference. This circuit includes two optional potentiometers and one optional resistor that can be used to adjust the gain, offset, and bipolar zero errors in a manner similar to that described in the Bipolar Configuration section. Use −5.000000 V and +4.999847, as the output values.

The AD660 can also be used with the AD587 10 V reference, using the same configuration shown in Figure 12 to produce a ±10 V output. The highest grade AD587UQ is specified at 5 ppm/°C, which is a 3× improvement over the AD660 internal reference.

Figure 13 shows the AD660 using the AD688 precision ±10 V reference, in the unipolar configuration. The highest grade AD688BQ is specified with a temperature coefficient of 1.5 ppm/°C. The ±10 V output is also ideal for providing precise biasing for the offset trim resistor, R4.

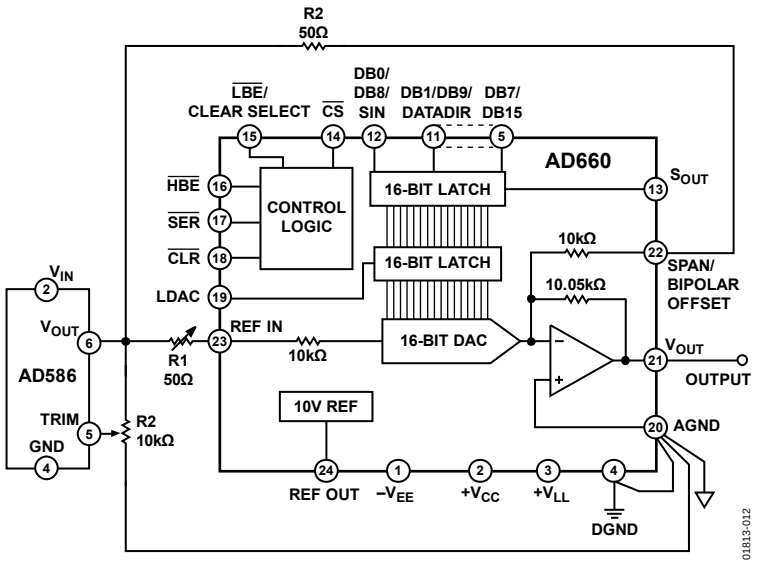


Figure 12. Using the AD660 with the AD586 5 V Reference

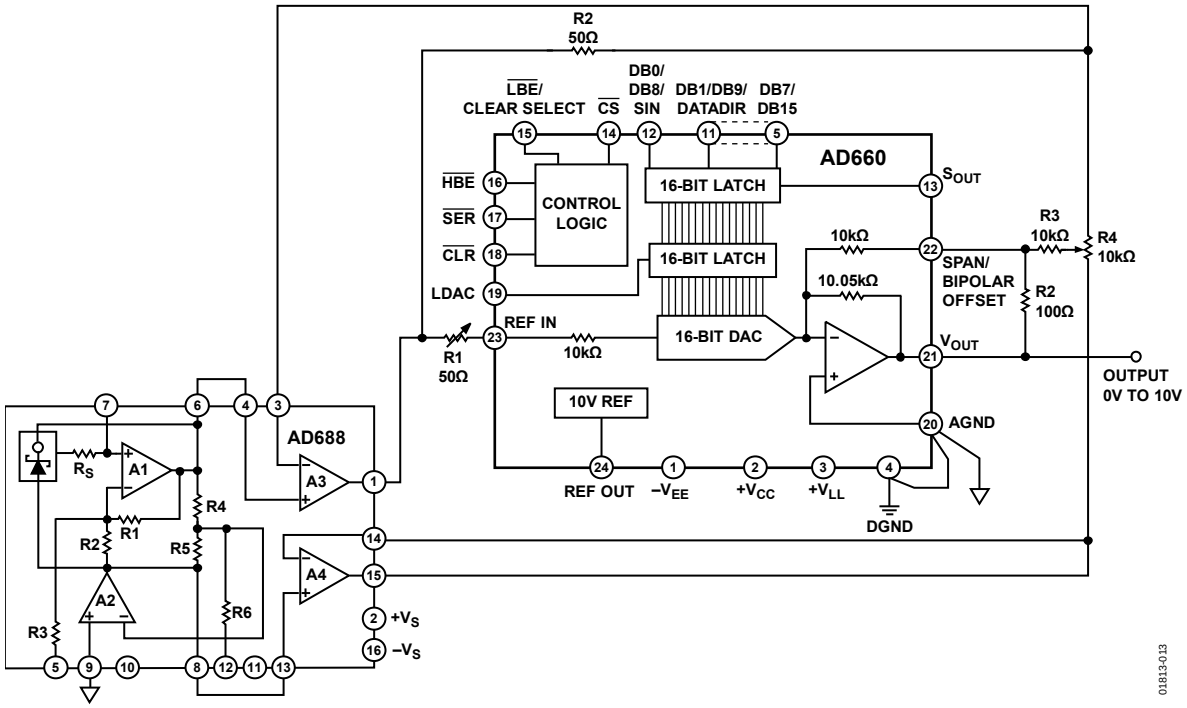


Figure 13. Using the AD660 with the AD688 High Precision ±10 V Reference

OUTPUT SETTLING AND GLITCH

The AD660 output buffer amplifier typically settles to within 0.0008% FS (1/2 LSB) of its final value in 8 µs for a full-scale step. Figure 14 and Figure 15 show settling for a full-scale and an LSB step, respectively, with a 2 kΩ, 1000 pF load applied. The guaranteed maximum settling time at 25°C for a full-scale step is 13 µs with this load. The typical settling time for a 1 LSB step is 2.5 µs.

The digital-to-analog glitch impulse is specified as 15 nV-s typical. Figure 16 shows the typical glitch impulse characteristic at the 011…111 to 100…000 code transition when loading the second rank register from the first rank register.

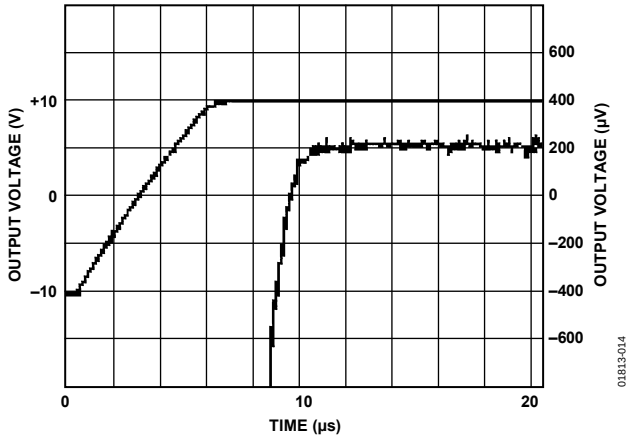


Figure 14. –10 V to +10 V Full-Scale Step Settling

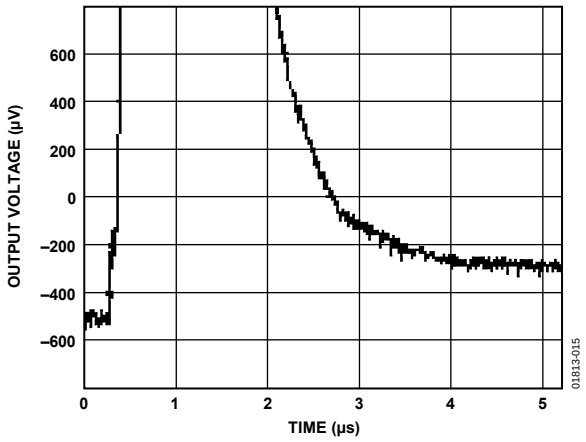


Figure 15. LSB Step Settling

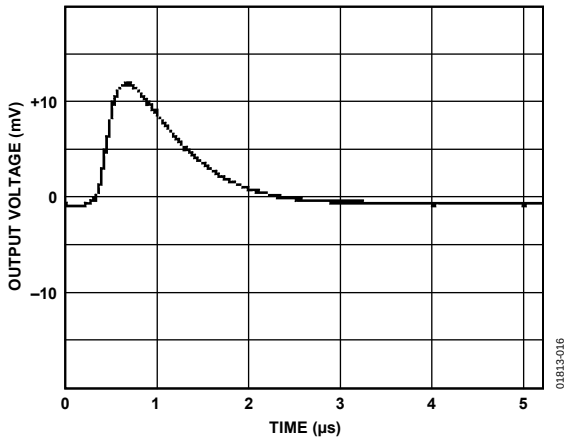


Figure 16. Output Characteristics

DIGITAL CIRCUIT DETAILS

The AD660 has several dual-use pins that allow flexible operation while maintaining the lowest possible pin count and consequently the smallest package size. The user should, therefore, pay careful attention to the following information when applying the AD660.

Data can be loaded into the AD660 in serial or byte mode, described as follows.

Serial mode operation is enabled by bringing $\overline{SER}$ (Pin 17) low. This changes the function of DB0 (Pin 12) to that of the serial input pin, SIN. It also changes the function of DB1 (Pin 11) to a control input that tells the AD660 whether the serial data is going to be loaded MSB or $\overline{LSB}$ first.

In serial mode, $\overline{HBE}$ and $\overline{LBE}$ are effectively disabled except for the dual function of $\overline{LBE}$, which is to control whether the asynchronous clear function goes to unipolar or bipolar zero. (A low on $\overline{LBE}$, when $\overline{CLR}$ is strobed, sends the DAC output to unipolar zero, a high to bipolar zero.) The AD660 does not recognize the status of HBE when in serial mode.

Data is clocked into the input register on the rising edge of $\overline{CS}$, as shown in Figure 3. The data then resides in the first rank latch and can be loaded into the DAC latch by taking LDAC high. This causes the DAC to change to the appropriate output value.

It should be noted that the $\overline{CLR}$ function clears the DAC latch but does not clear the first rank latch. Therefore, the data that was previously residing in the first rank latch can be reloaded simply by bringing LDAC high after the event that necessitated $\overline{CLR}$ to be strobed has ended. Alternatively, new data can be loaded into the first rank latch if desired.

The serial out pin (S_{OUT}) can be used to daisy-chain several DACs together in multiDAC applications to minimize the number of isolators being used to cross an intrinsic safety barrier. The first rank latch acts like a 16-bit shift register, and repeated strobing of $\overline{CS}$ shifts the data out through S_{OUT} and into the next DAC. Each DAC in the chain requires its own LDAC signal unless all of the DACs are to be updated simultaneously.

Byte mode operation is enabled simply by keeping $\overline{SER}$ high, which configures DB0 to DB7 as data inputs. In this mode, $\overline{HBE}$ and $\overline{LBE}$ are used to identify the data as either the high byte or the low byte of the 16-bit input word. (The user can load the data, in any order, into the first rank latch.) As in the serial mode case, the status of $\overline{LBE}$, when $\overline{CLR}$ is strobed, determines whether the AD660 clears to unipolar or bipolar zero. Therefore, when in byte mode, the user must take care to set $\overline{LBE}$ to the desired status before strobing $\overline{CLR}$. (In serial mode the user can simply hardware $\overline{LBE}$ to the desired state.)

Note that $\overline{CS}$ is edge triggered. $\overline{HBE}$, $\overline{LBE}$, and LDAC are level triggered.

MICROPROCESSOR INTERFACE

AD660 TO MC68HC11 (SPI BUS) INTERFACE

The AD660 interface to the Motorola SPI (serial peripheral interface) is shown in Figure 17. The MOSI, SCK, and $\overline{SS}$ pins of the 68HC11 are respectively connected to the DB0/DB8/SIN, $\overline{CS}$, and LDAC pins of the AD660. The $\overline{SER}$ pin of the AD660 is tied low causing the first rank latch to be transparent. The majority of the interfacing issues are taken care of in the software initialization. A typical routine such as the one shown in the Software Initialization Example begins by initializing the state of the various SPI data and control registers.

The most significant data byte (MSBY) is then retrieved from memory and processed by the SENDAT subroutine. The $\overline{SS}$ pin is driven low by indexing into the PORTD data register and clearing Bit 5. This causes the 2nd rank latch of the AD660 to become transparent. The MSBY is then set to the SPI data register where it is automatically transferred to the AD660.

The HC11 generates the requisite eight clock pulses with data valid on the rising edges. After the most significant byte is transmitted, the least significant byte (LSBY) is loaded from memory and transmitted in a similar fashion. To complete the transfer, the LDAC pin is driven high, latching the complete 16-bit word into the AD660.

Software Initialization Example

```
INIT    LDAA    #$2F        ; SS = I; SCK = 0; MOSI
                            = I
        STAA    PORTD       ;SEND TO SPI OUTPUTS
        LDAA    #$38        ; SS, SCK,MOSI = OUTPUTS
        STAA    DDRD        ;SEND DATA DIRECTION
                            INFO
        LDAA    #$50        ;DABL INTRPTS,SPI IS
                            MASTER & ON
        STAA    SPCR        ;CPOL = 0, CPHA = 0,1MHZ
                            BAUD RATE
NEXTPT  LDAA    MSBY        ;LOAD ACCUM WITH UPPER 8
                            BITS
        BSR     SENDAT      ;JUMP TO DAC OUTPUT
                            ROUTINE
        JMP     NEXTPT      ;INFINITE LOOP
SENDAT  LDY     #$1000      ;POINT AT ON-CHIP
                            REGISTERS
        BCLR    $08,Y,$20   ;DRIVE SS (LDAC) LOW
        STAA    SPDR        ;SEND MS-BYTE TO SPI
                            DATA REG
WAIT1   LDAA    SPSR        ;CHECK STATUS OF SPIE
        BPL     WAIT1       ;POLL FOR END OF X-
                            MISSION
        LDAA    LSBY        ;GET LOW 8 BITS FROM
                            MEMORY
        STAA    SPDR        ;SEND LS-BYTE TO SPI
                            DATA REG
WAIT2   LDAA    SPSR        ;CHECK STATUS OF SPIE
        BPL     WAIT2       ;POLL FOR END OF X-
                            MISSION
        BSET    $08,Y,$20   ;DRIV SS HIGH TO LATCH
                            DATA
        RTS
```

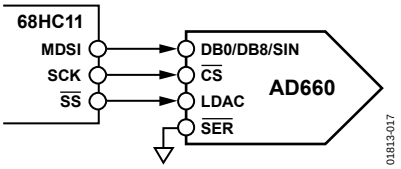


Figure 17. AD660 to 68HC11 (SPI) Interface

AD660 TO MICROWIRE INTERFACE

The flexible serial interface of the AD660 is also compatible with the National Semiconductor MICROWIRE™ interface. The MICROWIRE interface is used on microcontrollers, such as the COP400 and COP800 series of processors. A generic interface to the MICROWIRE interface is shown in Figure 18. The G1, SK, and SO pins of the MICROWIRE interface are respectively connected to the LDAC, $\overline{CS}$ and DB0/DB8/SIN pins of the AD660.

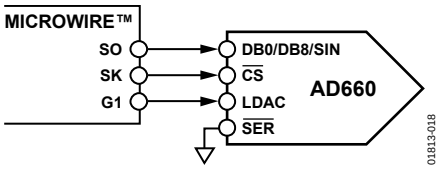


Figure 18. AD660 to MICROWIRE Interface

AD660 TO ADSP-210x FAMILY INTERFACE

The serial mode of the AD660 minimizes the number of control and data lines required to interface to digital signal processors (DSPs) such as the ADSP-210x family. The application in Figure 19 shows the interface between an ADSP-210x and the AD660. Both the TFS pin and the DT pins of the ADSP-210x should be connected to the $\overline{SER}$ and DB0 pins of the AD660, respectively. An inverter is required between the SCLK output and the $\overline{CS}$ input of the AD660 to ensure that data transmitted to the DB0 pin is valid on the rising edge of $\overline{CS}$.

The serial port (SPORT) of the DSP should be configured for alternate framing mode so that TFS complies with the word length framing requirement of $\overline{SER}$. Note that the INVTFS bit in the SPORT control register should be set to invert the TFS signal so that $\overline{SER}$ is the correct polarity. The LDAC signal, which must meet the minimum hold specification of t_{HIGH}, is easily generated by delaying the rising edge of $\overline{SER}$ with a 74HC74 flip-flop. The $\overline{CS}$ signal clocks the flip-flop, resulting in a delay of approximately one $\overline{CS}$ clock cycle.

In applications such as waveform generation, accurate timing of the output samples is important to avoid noise that is induced by jitter on the LDAC signal. In this example, the ADSP-210x is set up to use the internal timer to interrupt the processor at the precise and desired sample rate. When the timer interrupt occurs, the 16-bit data word of the processor is written to the transmit register (TXn). This causes the DSP to automatically generate the TFS signal and begin transmission of the data.

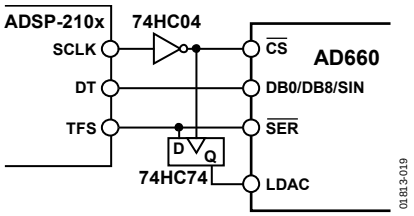


Figure 19. AD660 to ADSP-210x Interface

AD660 TO Z80 INTERFACE

Figure 20 shows a Zilog Z80 8-bit microprocessor connected to the AD660 using the byte mode interface. The double-buffered capability of the AD660 allows the microprocessor to independently write to the low and high byte registers, and update the DAC output. Processor speeds up to 6 MHz on the Z80 require no extra wait states to interface with the AD660 when using a 74ALS138 as the address decoder.

The address decoder analyzes the input-output address produced by the processor to select the function to be performed by the AD660, qualified by the coincidence of the input/output request ($\overline{\text{IORQ}}$) and write ($\overline{\text{WR}}$) pins. The least significant address bit (A0) determines if the low or high byte register of the AD660 is active. More significant address bits select between input register loading, DAC output update, and unipolar or bipolar clear.

A typical Z80 software routine begins by writing the low byte of the desired 16-bit DAC data to Address 0, followed by the high byte to Address 1. The DAC output is then updated by activating LDAC with a write to Address 2 (or Address 3). A clear to unipolar zero occurs on a write to Address 4, and a clear to bipolar zero is performed by a write to Address 5. The actual data written to Address 2 through Address 5 is irrelevant. The decoder can easily be expanded to control as many AD660 devices as required.

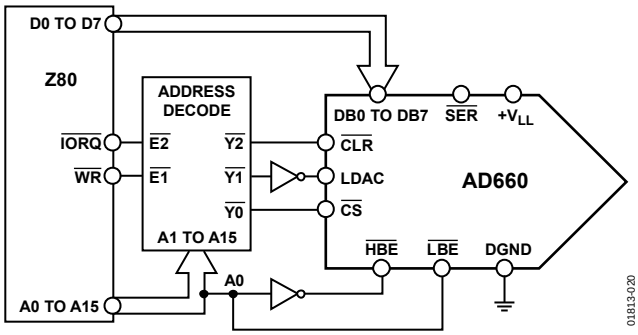


Figure 20. Connections for 8-Bit Bus Interface

NOISE

In high resolution systems, noise is often the limiting factor. A 16-bit DAC with a 10 V span has an LSB size of 153 μV (−96 dB). Therefore, the noise floor must remain below this level in the frequency range of interest. The noise spectral density of the AD660 is shown in Figure 21 and Figure 22. Figure 21 shows the DAC output noise voltage spectral density for a 20 V span excluding the reference. This figure shows the 1/f corner frequency at 100 Hz and the wideband noise to be below 120 nV/√Hz. Figure 22 shows the reference noise voltage spectral density and shows the reference wideband noise to be below 125 nV/√Hz.

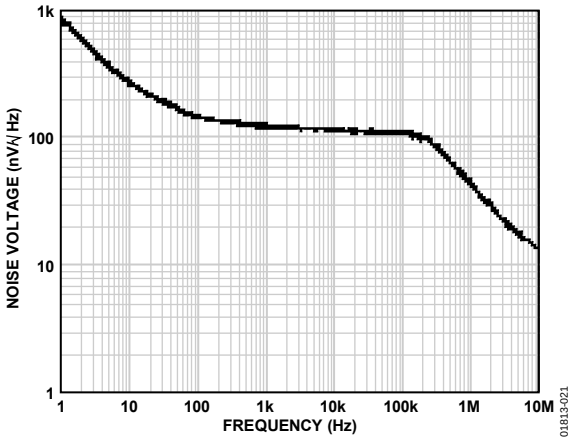


Figure 21. DAC Output Noise Voltage Spectral Density

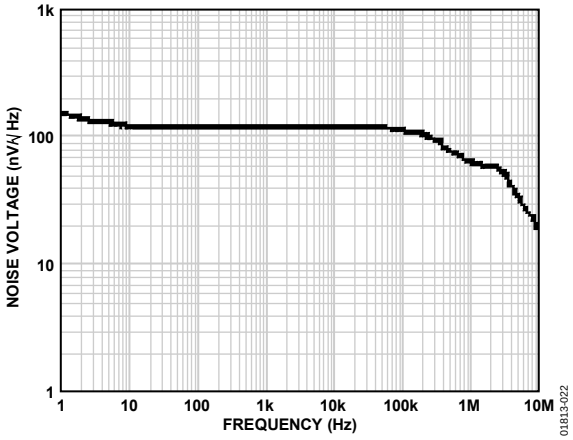


Figure 22. Reference Noise Voltage Spectral Density

BOARD LAYOUT

Designing with high resolution data converters requires careful attention to board layout. Trace impedance is the first issue. A 306 μA current through a 0.5 Ω trace develops a voltage drop of 153 μV, which is 1 LSB at the 16-bit level for a 10 V full-scale span. In addition to ground drops, inductive and capacitive coupling need to be considered, especially when high accuracy analog signals share the same board with digital signals. Finally, power supplies need to be decoupled to filter out ac noise.

Analog and digital signals should not share a common path. Each signal should have an appropriate analog or digital return routed close to it. Using this approach, signal loops enclose a small area, minimizing the inductive coupling of noise. Wide PC tracks, large gauge wire, and ground planes are highly recommended to provide low impedance signal paths. Separate analog and digital ground planes should also be used, with a single interconnection point to minimize ground loops. Analog signals should be routed as far as possible from digital signals and should cross them at right angles.

One feature that the AD660 incorporates to help the user layout is that the analog pins ($+V_{CC}$, $-V_{EE}$, REF OUT, REF IN, SPAN/BIPOLAR OFFSET, V_{OUT} and AGND) are adjacent to help isolate analog signals from digital signals.

SUPPLY DECOUPLING

The AD660 power supplies should be well filtered, well regulated, and free from high frequency noise. Switching power supplies are not recommended due to their tendency to generate spikes, which can induce noise in the analog system.

Decoupling capacitors should be used in very close layout proximity between all power supply pins and ground. A 10 μF tantalum capacitor in parallel with a 0.1 μF ceramic capacitor provides adequate decoupling. V_{CC} and V_{EE} should be bypassed to analog ground, while V_{LL} should be decoupled to digital ground.

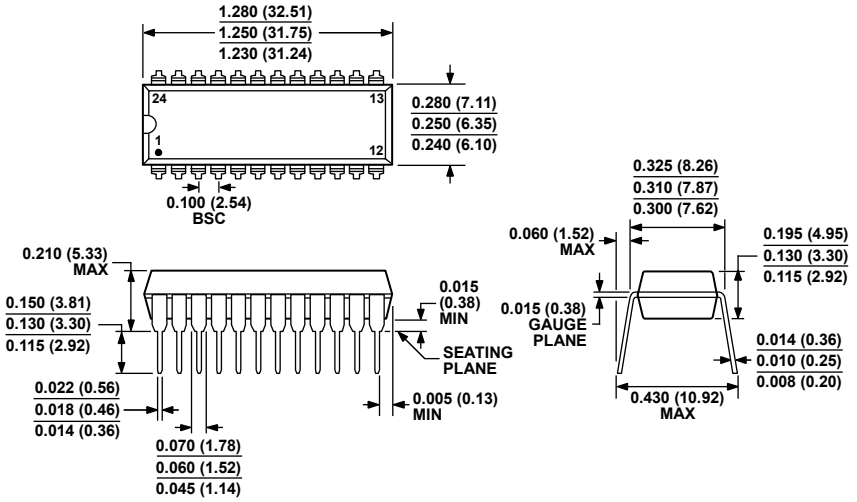
An effort should be made to minimize the trace length between the capacitor leads and the respective converter power supply and common pins. The circuit layout should attempt to locate the AD660, associated analog circuitry, and interconnections as far as possible from logic circuitry. A solid analog ground plane around the AD660 will isolate large switching ground currents. For these reasons, the use of wire wrap circuit construction is not recommended; careful printed circuit construction is preferred.

GROUNDING

The AD660 has two ground pins, designated analog ground (AGND) and digital ground (DGND.) The analog ground pin is the high quality ground reference point for the device. Any external loads on the output of the AD660 should be returned to analog ground. If an external reference is used, this should also be returned to the analog ground.

If a single AD660 is used with separate analog and digital ground planes, connect the analog ground plane to AGND and the digital ground plane to DGND keeping lead lengths as short as possible. Then connect AGND and DGND together at the AD660. If multiple AD660 devices are used or the AD660 shares analog supplies with other components, connect the analog and digital returns together once at the power supplies rather than at each chip. This single interconnection of grounds prevents large ground loops and consequently prevents digital currents from flowing through the analog ground.

OUTLINE DIMENSIONS



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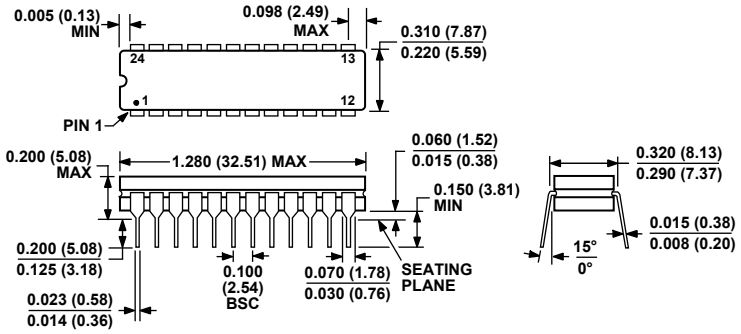
CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN. CORNER LEADS MAY BE CONFIGURED AS WHOLE OR HALF LEADS.

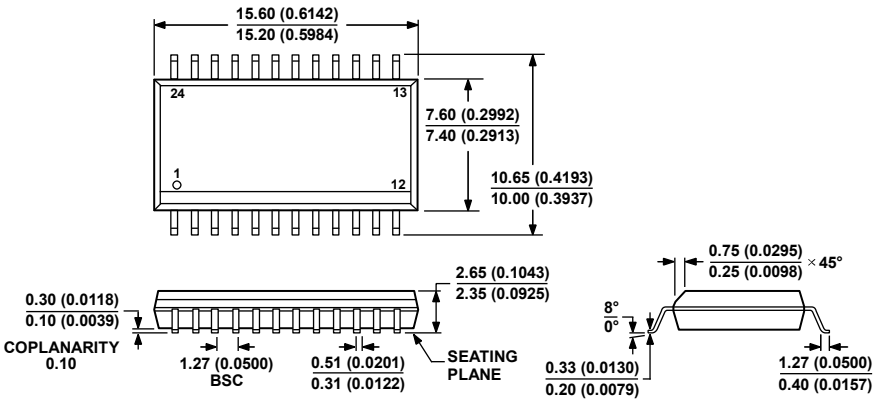
071006-A

Figure 23. 24-Lead Plastic Dual In-Line Package [PDIP]
Narrow Body
(N-24-1)
Dimensions shown in inches and (millimeters)



CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 24. 24-Lead Ceramic Dual In-Line Package [CERDIP]
(Q-24)
Dimensions shown in inches and (millimeters)



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REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

060706-A

Figure 25. 24-Lead Standard Small Outline Package [SOIC_W]
Wide Body
(RW-24)
Dimensions shown in millimeters and (inches)

ORDERING GUIDE

Model	Temperature Range	Gain TC Max ppm/°C	Package Description	Package Option
AD660AN	−40°C to +85°C	25	24-Lead PDIP	N-24-1
AD660ANZ[1]	−40°C to +85°C	25	24-Lead PDIP	N-24-1
AD660AR	−40°C to +85°C	25	24-Lead SOIC_W	RW-24
AD660AR-REEL	−40°C to +85°C	25	24-Lead SOIC_W	RW-24
AD660ARZ[1]	−40°C to +85°C	25	24-Lead SOIC_W	RW-24
AD660ARZ-REEL[1]	−40°C to +85°C	25	24-Lead SOIC_W	RW-24
AD660BN	−40°C to +85°C	15	24-Lead PDIP	N-24-1
AD660BNZ[1]	−40°C to +85°C	15	24-Lead PDIP	N-24-1
AD660BR	−40°C to +85°C	15	24-Lead SOIC_W	RW-24
AD660BR-REEL	−40°C to +85°C	15	24-Lead SOIC_W	RW-24
AD660BRZ[1]	−40°C to +85°C	15	24-Lead SOIC_W	RW-24
AD660BRZ-REEL[1]	−40°C to +85°C	15	24-Lead SOIC_W	RW-24
AD660SQ	−55°C to +125°C	25	24-Lead CERDIP	Q-24
AD660SQ/883B[2]	−55°C to +125°C			

[1] Z = RoHS Compliant Part.
[2] For further details, refer to the AD660SQ/883B military data sheet.

NOTES

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D01813-0-6/08(B)

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